

AOZ32033AQI

Coil Driver for Wireless Charger Transmitter with Slew-Rate Control

General Description

The AOZ32033AQI is an integrated half-bridge solution with intelligent slew-rate control for wireless charger application. The device includes the high-side, low-side N-channel MOSFETs and its driver circuit. Typically, it's dedicated for the design of wireless charger transmitter circuit which is composed of full-bridge topology with resonant tank circuit to get best efficiency of power converter.

The AOZ32033AQI provides adjustable gate drive sink and source current control, by doing this control methodology, it's able to optimize EMI and driver losses to improve overall efficiency performance. Moreover, the features of AOZ32033AQI have multiple protection functions such as V_{CC} UVLO, over temperature protection to make the design more robust.

The AOZ32033AQI is available in a 3mm×3mm QFN-18L package and is rated over a -40°C to +85°C ambient temperature range.

Features

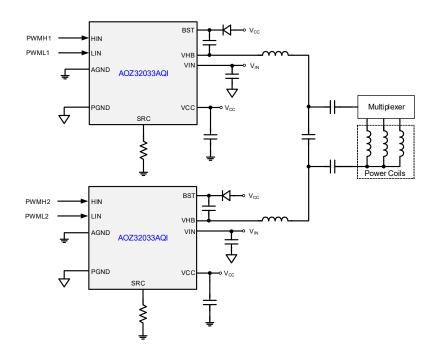
- Maximum input voltage 30V
 - -Support 12V & 24V voltage rail system
- 15W~30W coil driver
 - For wireless charger transmitter circuit
- Slew-rate control to improve EMI performance
- Integrated bootstrap diode
- Support protectiond
 - -OTP, UVLO
- Thermally enhanced 18-pin 3×3 QFN

Applications

Wireless charger TX



Typical Application (Wireless Charger TX)





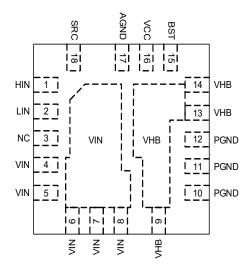
Ordering Information

Part Number	Ambient Temperature Range	Package	Environmental	
AOZ32033AQI	-40°C to +85°C	18-Pin 3x3 QFN	Green	



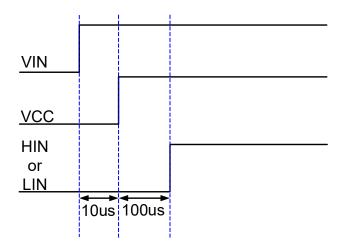
All AOS products are offered in packages with Pb-free plating and compliant to RoHS standards. Please visit http://www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

Pin Configuration



18-Pin 3mm x 3mm QFN

Start-up Sequence



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Pin Description

Pin Number	Pin Name	Pin Function
1	HIN	PWM Input for High-Side MOSFET.
2	LIN	PWM Input for Low-Side MOSFET.
3	NC	No connect
4, 5, 6, 7, 8	VIN	Supply Input. All VIN pins must be connected together.
9, 13, 14	VHB	Switching Node for Half-Bridge. All VHB must be connected together.
10, 11, 12	PGND	Power Ground.
15	BST	Bootstrap Capacitor Connection. Connect an external capacitor between BST and VHB for supplying high-side MOSFET.
16	VCC	Supply Input for Analog Functions. Bypass VCC to AGND with a 0.1uF~10uF ceramic capacitor and as close to VCC pin as possible
17	AGND	Analog Ground.
18	SRC	Slew-Rate Control to Adjust Driver Speed of Internal MOSFET.



Absolute Maximum Ratings⁽¹⁾

Parameter	Rating
VIN to AGND	-0.3V to 30V
VHB to AGND	-0.3V to 30V
BST to AGND	-0.3V to 40V
BST to VHB	-0.3 to 6V
SRC, VCC to AGND	-0.3V to 6V
PGND to AGND	-0.3V to +1V
Junction Temperature (T _J)	+150°C
Storage Temperature (T _S)	-65°C to +150°C
ESD Rating	±2kV

Notes:

- 1. Exceeding the Absolute Maximum ratings may damage the device.
- 2. The device is not guaranteed to operate beyond the Maximum Operating ratings.

Recommend Operating Ratings⁽²⁾

Parameter	Rating
Supply Voltage (V _{IN})	3.8V to 30V
Supply Voltage (V _{CC})	4.75V to 5.5V
Ambient Temperature (T _A)	-40°C to +85°C
Package Thermal Resistance	
(Θ_{JA})	40°C/W
(⊝ _{JC})	0.6°C/W

Electrical Characteristics

 $T_A = -40$ °C to 85°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{UVLO_R}	Vcc UVLO Rising	V _{IN} =12V, Vcc increase, Monitor SRC from low to high		4.3		٧
V _{UVLO_F}	Vcc UVLO Falling	V _{IN} =12V, Vcc decrease, Monitor SRC from high to low		4.2		V
V _{B_UVLO_R}	V _{BST} -V _{HB} UVLO Rising	$V_{\rm IN}$ =20V, ($V_{\rm BST}$ - $V_{\rm HB}$) increase, Monitor $V_{\rm HB}$ from low to high		4.3		V
V _{B_UVLO_F}	V _{BST} -V _{HB} UVLO Falling	$V_{\rm IN}$ =20V, ($V_{\rm BST}$ - $V_{\rm HB}$) decrease, Monitor $V_{\rm HB}$ from high to low		4.2		V
I _{VIN_QC}	I _{VIN} Quiescent Current	V_{IN} =12V, V_{CC} =5V, HIN=LIN=0V, SRC=100k Ω		30		μA
I _{VCC_QC}	I _{VCC} Quiescent Current	V_{IN} =12V, V_{CC} =5V, HIN=LIN=0V, SRC=100k Ω		200		μA
I _{BST-VHB_QC}	I _{BST-VHB} Quiescent Current	HIN/LIN=0V, V _{HB} =1V, (V _{BST} -V _{HB})=5V, Monitor (V _{BST} -V _{HB}) Current			0.2	mA
V _{HLIN_L}	HIN/LIN Logic Low Voltage	V _{IN} =12V	0		1.2	V
V _{HLIN_H}	HIN/LIN Logic High Voltage	V _{IN} =12V	2.2		5.5	V
R _{HLIN_IN}	HIN/LIN Input Pull Low Impedance			280		kΩ
t _{HIN_RP}	HIN Rising Propagation Delay	V_{IN} =10V, V_{CC} =5V, SRC=20kΩ, VHB to GND=100Ω, HIN=Low to High, Monitor V_{HB} Low to High		55		ns
t _{HIN_FP}	HIN Falling Propagation Delay	V_{IN} =10V, V_{CC} =5V, SRC=20kΩ, VHB to GND=100Ω, HIN=High to Low, Monitor V_{HB} High to Low		75		ns
t _{LIN_RP}	LIN Rising Propagation Delay	V_{IN} =10V, V_{CC} =5V, SRC=20kΩ,VHB to VIN=100Ω, LIN=Low to High, Monitor V_{HB} High to Low		45		ns
t _{LIN_FP}	LIN Falling Propagation Delay	V_{IN} =10V, V_{CC} =5V, SRC=20k Ω ,VHB to VIN=100 Ω , LIN=High to Low, Monitor V_{HB} Low to High		70		ns



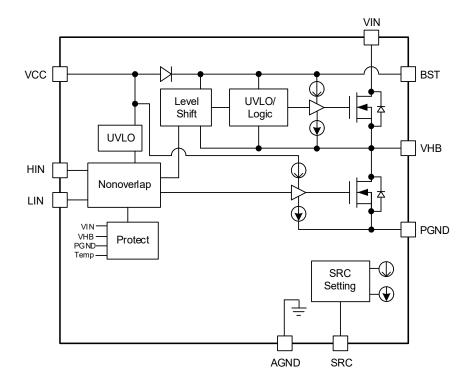
Electrical Characteristics

 T_A = -40°C to 85°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
T _{DM_R}	Delay Matching Rising	Difference between t _{HIN_RP} and t _{LIN_RP}		10		ns
T _{DM_F}	Delay Matching Falling	Difference between t _{HIN_FP} and t _{LIN_FP}		5		ns
V _{SRC}	SRC	V_{IN} =12V, V_{CC} =5V, SRC=20k Ω	0.97	1	1.03	V
I _{SRC_MIN}	SRC Min. Source Current	V _{IN} =12V, V _{CC} =5V, SRC=4V		0.5		μΑ
I _{SRC_MAX}	SRC Max. Source Current	V _{IN} =12V, V _{CC} =5V, SRC=0.8V		140		μΑ
SR _{HIN_R}	HIN Rising Slew Rate (SRC=20kΩ)	VIN=10V, V _{CC} =5V, V _{HB} to GND=100Ω, HIN=Low to High, Monitor V _{HB} Rising Slew Rate		0.85		V/ns
SR _{HIN_F}	HIN Falling Slew Rate (SRC=20kΩ)	VIN=10V, V_{CC} =5V, V_{HB} to GND=100Ω, HIN=High to Low, Monitor V_{HB} Falling Slew Rate		0.06		V/ns
SR _{LIN_R}	LIN Rising Slew Rate (SRC=20kΩ)	VIN=10V, V_{CC} =5V, V_{HB} to VIN=100 Ω , LIN=High to Low, Monitor V_{HB} Rising Slew Rate		0.07		V/ns
SR _{LIN_F}	LIN Falling Slew Rate (SRC=20kΩ)	VIN=10V, V_{CC} =5V, V_{HB} to VIN=100Ω, LIN=Low to High Monitor V_{HB} Falling Slew Rate		1.3		V/ns
R _{H_ON}	V _{IN} -V _{HB} RON	V_{IN} =12V, V_{CC} =5V, HIN=5V, $(V_{BST}$ - $V_{HB})$ =5V, I_{VHB} =1A		11		mΩ
R _{L_ON}	V _{HB} -PGND RON	V _{IN} =12V, V _{CC} =5V, LIN=5V, PGND=0, I _{VHB} =1A		11		mΩ
V_{SD}	Boost Diode Forward Voltage	Forward Current = 2mA		0.4		V
T _{OTP}	OTP	V _{IN} =12V, V _{CC} =5V		150		°C



Functional Block Diagram





Typical Performance Characteristics

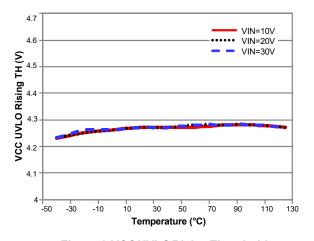


Figure 1.VCCUVLORising Threshold

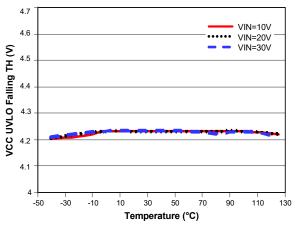


Figure 3. VCC UVLO Falling Threshold

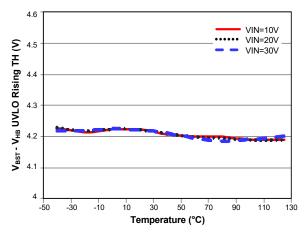


Figure 5. V_{BST} - V_{HB} UVLO Rising Threshold

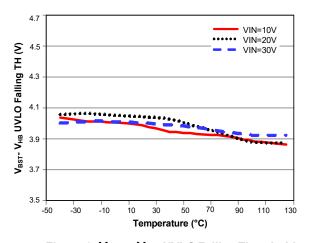


Figure 2. V_{BST} - V_{HB} UVLO Falling Threshold

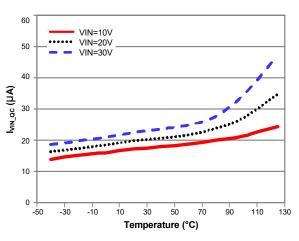


Figure 4. Input Standby Current

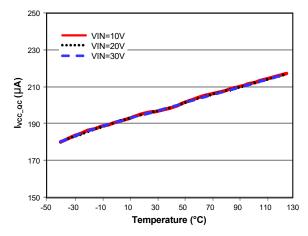


Figure 6. V_{CC} Standby Current

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Typical Performance Characteristics (Continued)

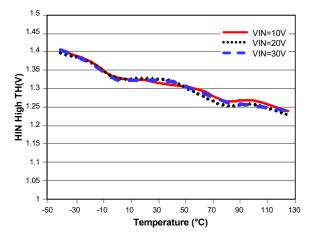


Figure 7. HIN High Threshold

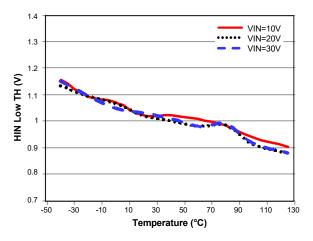


Figure 9. HIN Low Threshold

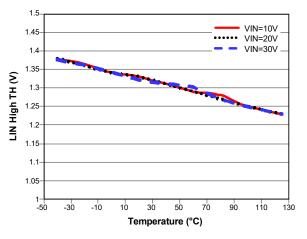


Figure 8. LIN High Threshold

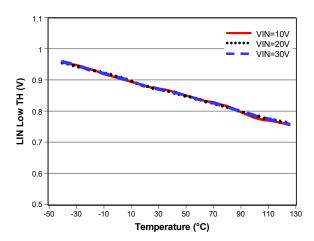


Figure 10. LIN Low Threshold

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Detailed Description

The AOZ32033AQI is an integrated half-bridge solution with intelligent slew-rate control for wireless charger application. The device includes the high-side, low-side N-channel MOSFETs and its driver circuit. Typically, it's dedicated for the design of wireless charger transmitter circuit which is composed of full-bridge topology with resonant tank circuit to get best efficiency of power converter.

The AOZ32033AQI provides adjustable gate drive sink and source current control, by doing this control methodology, it's able to optimize EMI and driver losses to improve overall efficiency performance.

In addition, the AOZ32033AQI provides several fault protections, such as UVLO, OTP and non-overlapping mechanism.

The AOZ32033AQI is available in 18-pin 3mm×3mm QFN package.

Non-overlapping

For forbidding shoot-through, HIN or LIN is invalid when HIN or LIN goes high state before other one. For example, low-side gate state keeps low regardless of the state of LIN when HIN is high at first, and vice versa.

Adjustable Source/Sink Current

It's hard to meet all of EMI specifications in different applications. So, AOZ32033AQI provides external adjustable resistors for tuning gate drive source and sink current.

SRC is used to tune gate drive source and sink current, respectively. A resistor connects between SRC pin and GND to setting gate drive source / sink current by internal current mirror, as illustrated Fig. 11. Source and sink current use maximum capability to drive when SRC pin is floating or the voltage on SRC pin is exceed 4V.

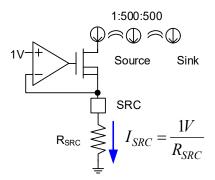


Figure 11. Source/Sink Current Implement Waveform

In addition, source and sink current controls are implemented only during MOSFET Miller effect and VGS >1V, as illustrated Fig. 12.

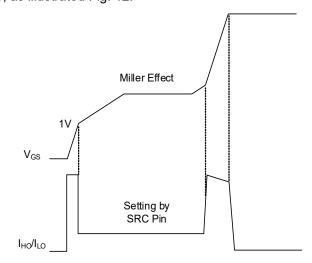


Figure 12. Source /Sink Current Implement Waveform



Layout Considerations

Several layout tips are listed below for the best electric and thermal performance.

- The VIN pins and pad are connected to internal high side switch drain. They are also low resistance thermal conduction path. Connected a large copper plane to VIN pins to help thermal dissipation.
- Input capacitors should be connected to the VIN pins and the PGND pins as close as possible to reduce the switching spikes.
- The VHB pins and pad are connected to internal low side switch drain. They are low resistance thermal conduction path and most noisy switching node. Connected a large copper plane to VHB pins to help thermal dissipation.
- 4. Decoupling capacitor C_{VCC} should be connected to V_{CC} and AGND as close as possible.
- Bootstrap capacitor C_{BST} should be connected to VBST and VHB as close as possible.

- 6. A ground plane is preferred; PGND and AGND must be connected to the ground plane through vias.
- 7. Keep sensitive signal traces such as feedback trace and digital signals far away from the VHB pins.

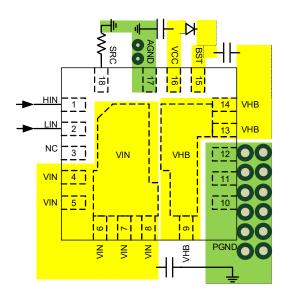
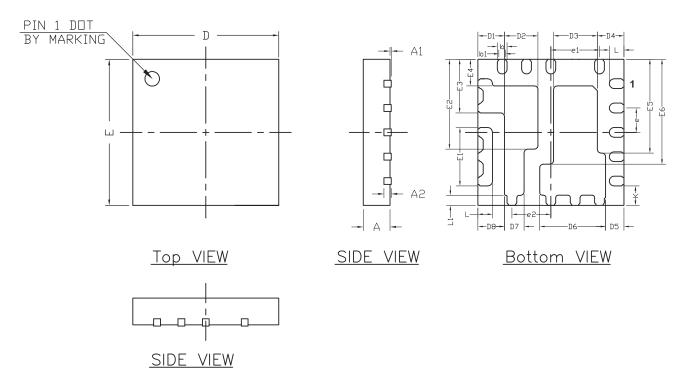


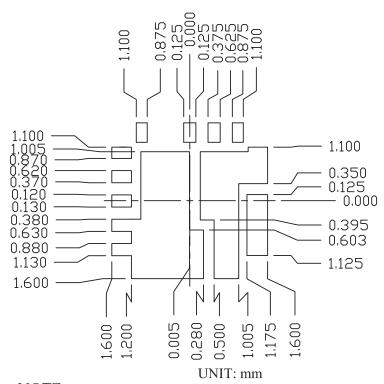
Figure 13. Layout Placement



Package Dimensions, QFN3x3-18L







SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENS	IONS IN MIL	LIMETERS				
	MIN	NOM	MAX	MIN	MIN NOM					
Α	0.45	0.55	0.65	0.018	0.022	0.026				
A1	0.00	-	0.05	0.000	-	0.002				
A2	0.10	0.15	0.20	0.004	0.006	0.008				
E	2.90	3.00	3.10	0.114	0.118	0.122				
E1	1.15	1.20	1.25	0.045	0.047	0.049				
E2	1.80	1.85	1.90	0.071	0.073	0.075				
E3	1.00	1.10	1.20	0.039	0.043	0.047				
E4	0.45	0.55	0.65	0.018	0.021	0.025				
E5	1.88	1.93	1.98	0.074	0.076	0.078				
E6	2.10	2.15	2.20	0.083	0.085	0.087				
D	2.90	3.00	3.10	0.114	0.118	0.122				
D1	0.45	0.55	0.65	0.018	0.021	0.025				
D2	0.64	0.69	0.74	0.025	0.027	0.029				
D3	0.85	0.90	0.95	0.033	0.035	0.037				
D4	0.45	0.55	0.65	0.018	0.021	0.025				
D5	0.33	0.38	0.43	0.013	0.015	0.017				
D6	1.30	1.35	1.40	0.051	0.053	0.055				
D7	0.35	0.40	0.45	0.014	0.016	0.018				
D8	0.50	0.55	0.60	0.019	0.021	0.023				
L	0.25	0.30	0.35	0.010	0.012	0.014				
L1	0.15	0.20	0.25	0.006	0.008	0.010				
b	0.15	0.20	0.25	0.006	0.008	0.010				
b1	0.09	0.14	0.19	0.004	0.006	0.007				
K	0.35	0.40	0.45	0.014	0.016	0.018				
е		0.50		0.020						
e1		1.00			0.039					
e2		0.80			0.031					

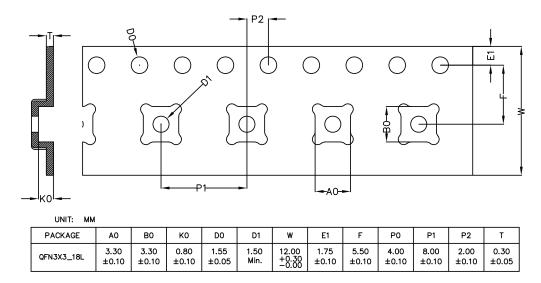
NOTE CONTROLLING DIMENSION IS MILLIMETER.

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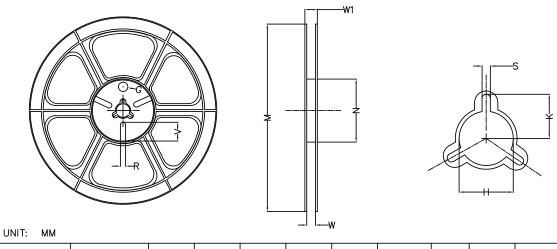


Tape and Reel Drawing, QFN3x3-18L

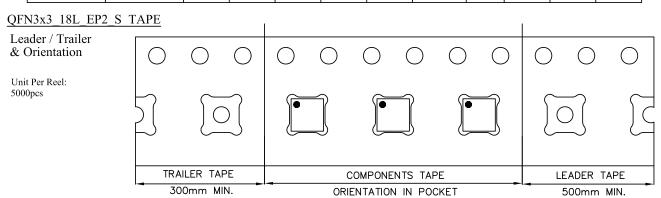
QFN3x3_18L_EP2_S Carrier Tape



QFN3x3_18L_EP2_S Reel

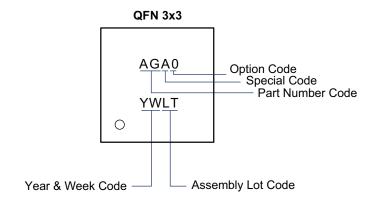


TAPE SIZE	REEL SIZE	М	N	W	W1	Н	S	К	G	R	٧
12 mm	ø330	ø330.00 ±2.00	ø101.6 ±2.00	12.40 +2.00 -0.00	12.40 +3.00 -0.20	ø13.20 ±0.30	1.70-2.60				





Part Marking



Note:

Assembly Location - YWLT/YWLT/YWLT

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